

PUB4702

Silicon n-channel power MOSFET

For switching

■ Features

- Avalanche energy capacity guaranteed
- High-speed switching
- Low ON resistance
- No secondary surrender
- Low-voltage drive
- Zener diodes built-in

■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-source surrender voltage	V_{DSS}	35 ± 10	V
Gate-source voltage (D-S short)	V_{GSS}	± 15	V
Drain current	I_D	± 1 ± 2	A
Avalanche energy capability ^{*2}	EAS	2.5	mJ
Power dissipation	P_D	15 3.5	W
$T_a = 25^\circ\text{C}$			
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to $+150$	$^\circ\text{C}$

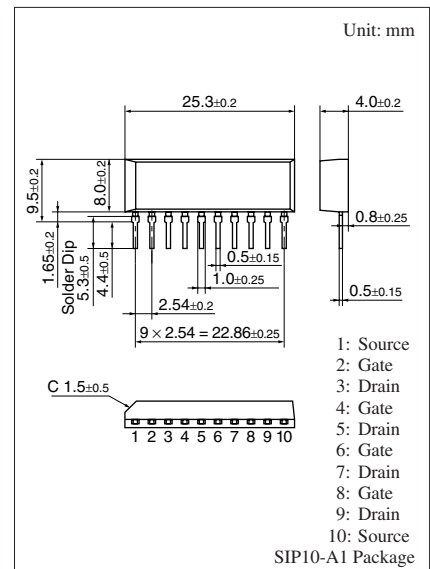
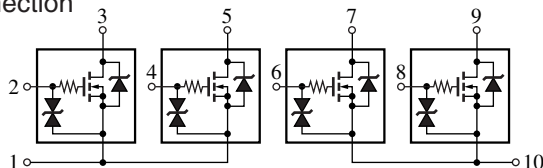
Note) *: $L = 5$ mH, $I_L = 1$ A, 1 pulse

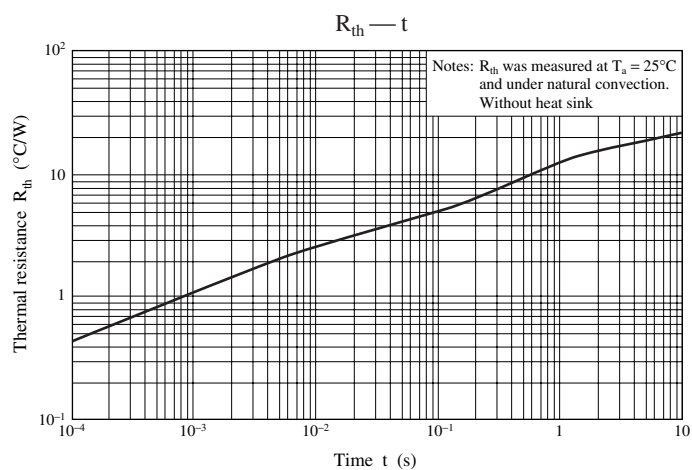
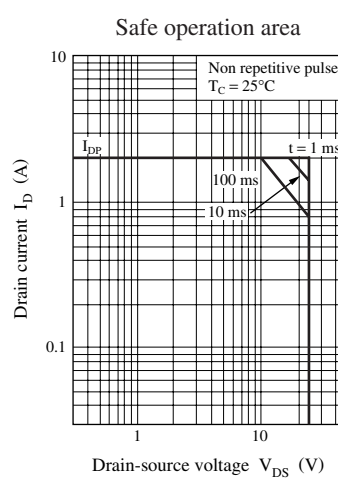
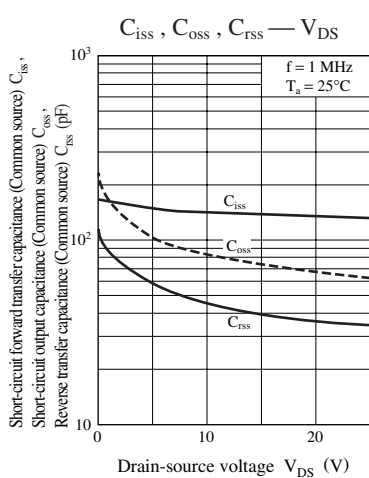
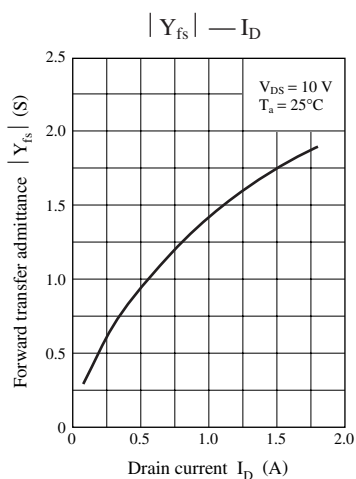
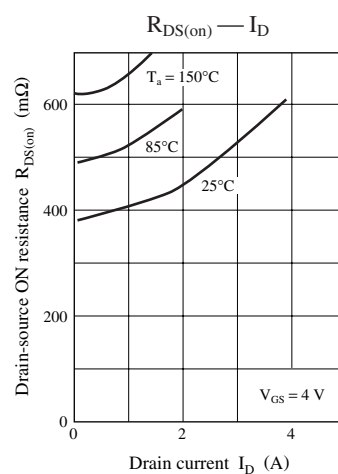
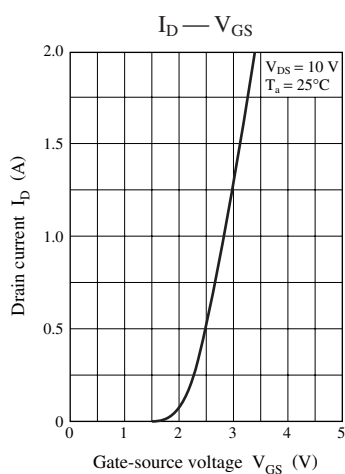
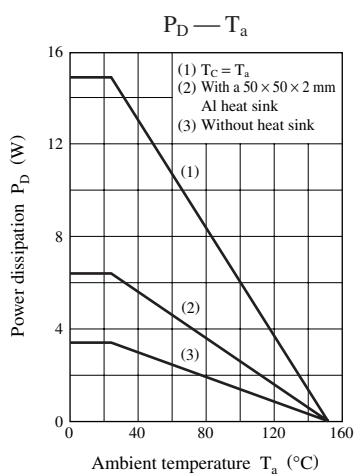
■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source surrender voltage	V_{DSS}	$I_D = 1$ mA, $V_{GS} = 0$	25		45	V
Gate threshold voltage	V_{th}	$V_{DS} = 10$ V, $I_D = 1$ mA	1.0		2.5	V
Diode forward voltage	V_{DF}	$I_{DR} = 1$ A, $V_{GS} = 0$			-1.5	V
Drain-source cutoff current (G-S short)	I_{DSS}	$V_{DS} = 25$ V, $V_{GS} = 0$			10	μA
Gate-source cutoff current (D-S short)	I_{GSS}	$V_{GS} = \pm 15$ V, $V_{DS} = 0$			± 10	μA
Drain-source ON resistance	$R_{DS(on)1}$	$V_{GS} = 10$ V, $I_D = 0.5$ A		220	380	$\text{m}\Omega$
	$R_{DS(on)2}$	$V_{GS} = 4$ V, $I_D = 0.5$ A		390	680	
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10$ V, $I_D = 0.5$ A	0.6	1.0		S
Short-circuit forward transfer capacitance (Common-source)	C_{iss}	$V_{DS} = 10$ V, $V_{GS} = 0$, $f = 1$ MHz		135		pF
Short-circuit output capacitance (Common-source)	C_{oss}			85		pF
Reverse transfer capacitance (Common-source)	C_{rss}			50		pF
Turn-on time	t_{on}	$V_{DD} = 25$ V, $I_D = 0.5$ A, $R_L = 50$ Ω		120		ns
Fall time	t_f	$V_{GS} = 10$ V		390		ns
Turn-off delay time	$t_{d(off)}$			800		ns

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

■ Internal Connection





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